

Application No. 10/673767
Page 3

Amendment
Attorney Docket No. 011.2B-11336-US01

Amendments To The Claims:

1. (Currently Amended) A polishing composition used in polishing a wafer edge, the polishing composition comprising:

silicon dioxide, wherein an average primary particle diameter D_{SA} of the silicon dioxide, which is obtained from a specific surface area of the silicon dioxide measured by a BET method, is at least 40 nm, wherein a 95th percentile diameter D_{95} of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes below which 95% (by volume) of all particles contained in the silicon dioxide are smaller, wherein a 5th percentile diameter D_5 of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 5% of the total of the volumes below which 5% (by volume) of all particles contained in the silicon dioxide are smaller, and wherein a ratio D_{95}/D_5 of the silicon dioxide, which is obtained by dividing the 95th percentile diameter D_{95} by the 5th percentile diameter D_5 , is no more than 3.8,

an alkaline compound,

a water-soluble polymer, and

water.

2. (Original) The polishing composition according to claim 1, wherein the average primary particle diameter D_{SA} is at least 60 nm.

3. (Original) The polishing composition according to claim 2, wherein the average primary particle diameter D_{SA} is at least 70 nm.

4. (Original) The polishing composition according to claim 1, wherein the ratio D_{95}/D_5 is no more than 3.6.

5. (Original) The polishing composition according to claim 4, wherein the ratio D_{95}/D_5 is no more than 3.4.

Application No. 10/673767
Page 4

Amendment
Attorney Docket No. 011.2B-11336-US01

6. (Original) The polishing composition according to claim 1, wherein the silicon dioxide is at least one silica selected from colloidal silica, fumed silica, and precipitated silica.
7. (Original) The polishing composition according to claim 6, wherein the silicon dioxide is colloidal silica.
8. (Original) The polishing composition according to claim 1, wherein the water-soluble polymer is at least one polymer selected from hydroxyethyl cellulose, polyvinyl alcohol, polyethylene oxide, and polyethylene glycol.
9. (Original) The polishing composition according to claim 8, wherein the water-soluble polymer is hydroxyethyl cellulose.
10. (Original) The polishing composition according to claim 1, wherein content of the water-soluble polymer in the polishing composition is from 0.0001 to 0.5 wt%.
11. (Original) The polishing composition according to claim 1, wherein the alkaline compound is at least one alkaline compound selected from potassium hydroxide, sodium hydroxide, potassium hydrogencarbonate, potassium carbonate, sodium hydrogencarbonate, sodium carbonate, tetramethylammonium hydroxide, ammonium hydrogencarbonate, ammonium carbonate, anhydrous piperazine, and piperazine hexahydrate.
12. (Currently Amended) A polishing composition used in polishing a wafer edge, the polishing composition comprising:
silicon dioxide, wherein an average primary particle diameter D_{SA} of the silicon dioxide, which is obtained from a specific surface area of the silicon dioxide measured by a BET method, is at least 40 nm, wherein a 95th percentile diameter D_{95} of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the

Application No. 10/673767
Page 5

Amendment
Attorney Docket No. 011.2B-11336-US01

volumes ~~below which 95% (by volume)~~ of all particles contained in the silicon dioxide are ~~smaller~~, wherein a 5th percentile diameter D_5 of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes ~~below which 5% (by volume)~~ of all particles contained in the silicon dioxide are ~~smaller~~, and wherein a value $D_{95}/D_5/D_{SA}$ of the silicon dioxide, which is obtained by dividing the 95th percentile diameter D_{95} by the 5th percentile diameter D_5 and further dividing the obtained ratio D_{95}/D_5 by the average primary particle diameter D_{SA} , is no more than 0.07,

an alkaline compound,
a water-soluble polymer, and
water.

13. (Original) The polishing composition according to claim 12, wherein the value $D_{95}/D_5/D_{SA}$ is no more than 0.06.

14. (Original) The polishing composition according to claim 13, wherein the value $D_{95}/D_5/D_{SA}$ is no more than 0.045.

15. (Original) The polishing composition according to claim 12, wherein the ratio D_{95}/D_5 is no more than 3.8.

16. (Original) The polishing composition according to claim 15, wherein the ratio D_{95}/D_5 is no more than 3.6.

17. (Original) The polishing composition according to claim 16, wherein the ratio D_{95}/D_5 is no more than 3.4.

18. (Currently Amended) A method of polishing a wafer, the method comprising:
preparing a polishing composition, wherein the polishing composition includes:
silicon dioxide, wherein an average primary particle diameter D_{SA} of the silicon

Application No. 10/673767
Page 6

Amendment
Attorney Docket No. 011.2B-11336-US01

dioxide, which is obtained from a specific surface area of the silicon dioxide measured by a BET method, is at least 40 nm, wherein a 95th percentile diameter D_{95} of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes below which 95% (by volume) of all particles contained in the silicon dioxide are smaller, wherein a 5th percentile diameter D_5 of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes below which 5% (by volume) of all particles contained in the silicon dioxide are smaller, and wherein a ratio D_{95}/D_5 of the silicon dioxide, which is obtained by dividing the 95th percentile diameter D_{95} by the 5th percentile diameter D_5 , is no more than 3.8;

an alkaline compound;

a water-soluble polymer; and

water; and

polishing a edge of the wafer using the polishing composition.

19. (Currently Amended) A method of polishing a wafer, the method comprising:

preparing a polishing composition, wherein the polishing composition includes:

silicon dioxide, wherein an average primary particle diameter D_{SA} of the silicon dioxide, which is obtained from a specific surface area of the silicon dioxide measured by a BET method, is at least 40 nm, wherein a 95th percentile diameter D_{95} of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes below which 95% (by volume) of all particles contained in the silicon dioxide are smaller, wherein a 5th percentile diameter D_5 of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes below which 5% (by volume) of all particles contained in the silicon dioxide are smaller, and wherein a value $D_{95}/D_5/D_{SA}$

Application No. 10/673767
Page 7

Amendment
Attorney Docket No. 011.2B-11336-US01

of the silicon dioxide, which is obtained by dividing the 95th percentile diameter D_{95} by the 5th percentile diameter D_5 and further dividing the obtained ratio D_{95}/D_5 by the average primary particle diameter D_{SA} , is no more than 0.07;

an alkaline compound;

water-soluble polymer; and

water; and

polishing a edge of the wafer using the polishing composition.

20. (Currently Amended) A method of polishing a wafer the method comprising:

preparing a polishing composition, wherein the polishing composition includes:

silicon dioxide, wherein an average primary particle diameter D_{SA} of the silicon dioxide, which is obtained from a specific surface area of the silicon dioxide measured by a BET method, is at least 40 nm, wherein a 95th percentile diameter D_{95} of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes below which 95% (by volume) of all particles contained in the silicon dioxide are smaller, wherein a 5th percentile diameter D_5 of the silicon dioxide is a diameter of a particle of the silicon dioxide, lastly integrated in integrating the volume of each particle of the silicon dioxide in ascending order until the integrated value reaches 95% of the total of the volumes below which 5% (by volume) of all particles contained in the silicon dioxide are smaller, wherein a ratio D_{95}/D_5 of the silicon dioxide, which is obtained by dividing the 95th percentile diameter D_{95} by the 5th percentile diameter D_5 , is no more than 3.8, and wherein a value $D_{95}/D_5/D_{SA}$ of the silicon dioxide, which is obtained by dividing the ratio D_{95}/D_5 by the average primary particle diameter D_{SA} , is no more than 0.07;

an alkaline compound;

a water-soluble polymer; and

water; and

polishing a edge of the wafer using the polishing composition.